

Parameter	Tr1 and Tr2
V_{CEO}	20V
V_{EBO}	12V
I _C	600mA
R ₁	10kΩ

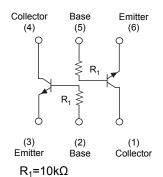
Outline SMT6 (3) (2) (1)

SOT-457 (SC-74)

Features

- 1) Built-In Biasing Resistors
- 2) Two DTC614T chips in one package.
- 3) Low saturation voltage, typically $V_{CE(sat)}$ =40mV at I_C / I_B =50mA / 2.5mA, makes these transistors ideal for muting circuits.
- 4) These transistors can be used at high current levels, $I_{\rm C}$ =600mA.
- 5) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 6) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 7) Lead Free/RoHS Compliant.

•Inner circuit



Application

Muting circuit

Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
IMH21	SMT6	2928	T110	180	8	3,000	H21

●Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Values	Unit
Collector-base voltage	V _{CBO} 20		V
Collector-emitter voltage	e V _{CEO} 20		V
Emitter-base voltage	V_{EBO}	12	V
Callegator augment	I _C	600	mA
Collector current	I _{CP} *1	1	Α
Power dissipation	P _D *2	300(Total) *3	mW
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	−55 to +150	°C

●Electrical characteristics (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	20	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	20	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 50μA	12	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 20V	-	1	0.5	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 12V	ı	ı	0.5	μΑ
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C}$ / $I_{\rm B}$ = 50mA / 2.5mA	ı	40	150	mV
DC current gain	h _{FE}	V_{CE} = 5V, I_{C} = 50mA	820	-	2700	-
Input resistance	R ₁	-	7	10	13	kΩ
Transition frequency	f _T *4	$V_{CE} = 10V, I_{E} = -50mA$ f = 100MHz	-	150	-	MHz
Output ON Resistance	R _{on}	$V_1 = 5V$ $R_L = 1k\Omega, f = 1kHz$	-	0.9	-	Ω

^{*1} P_W=10ms, Single pulse

^{*2} Each terminal mounted on a reference footprint

^{*3 200}mW per element must not be exceeded.

^{*4} Characteristics of built-in transistor

●Electrical characteristic curves(Ta = 25°C)

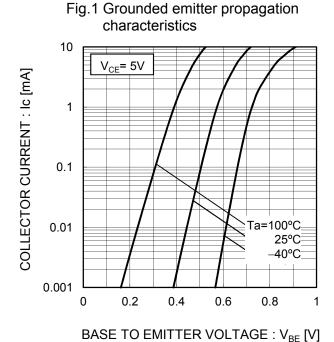


Fig.2 Grounded emitter output characteristics 0.9mA 600 0.8mA Ta=25°C 0.7mA 0.6mA 0.5mA 400 0.4mA 0.3mA 0.2mA 200 0.1mA 0 0A 2 10

COLLECTOR CURRENT : I_C [mA]

COLLECTOR TO EMITTER VOLTAGE : $V_{CE}[V]$

Fig.4 Collector-emitter saturation voltage

Fig.3 DC Current gain vs. Collector Current

10000

VcE=5V

Ta=100°C

25°C

40°C

-40°C

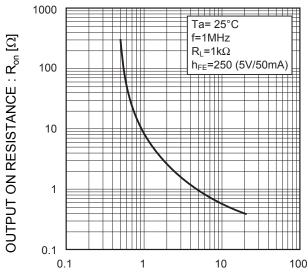
COLLECTOR CURRENT: I_C [mA]

vs. Collector Current 10000 $I_C/I_B=20$ COLLECTOR SATURATION VOLTAGE: V_{CE(sat)} [mV] 1000 100 Ta= 100°C 25°C 40°C 10 0.1 10 100 1000 COLLECTOR CURRENT : I_C [mA]

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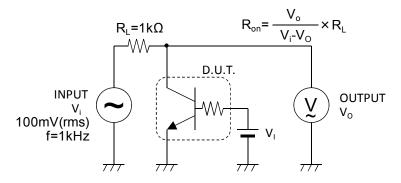
●Electrical characteristic curves(Ta = 25°C)

Fig.5 Output ON resistance vs. input voltage

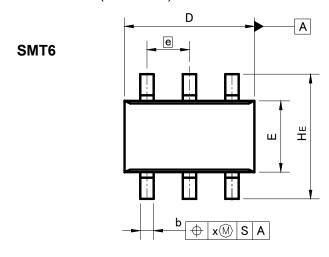


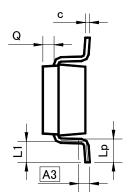
INPUT VOLTAGE: V_I [V]

Fig.6 Ron measurement circuit.

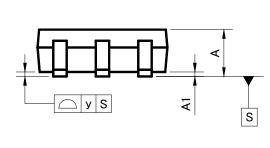


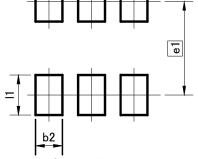
●Dimensions (Unit : mm)





е





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0.000	0.004	
A3	0.5	25	0.010		
b	0.25	0.40	0.010	0.016	
С	0.09	0.25	0.004	0.010	
D	2.80	3.00	0.110	0.118	
Е	E 1.50	1.80	0.059	0.071	
е	0.9	95	0.0	37	
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20		0.008	
У	_	0.10	_	0.004	

DIM	MILIMI	ETERS	INCHES		
	DIM	MIN	MAX	MIN	MAX
	b2		0.60	ı	0.024
	e1	2.	10	0.0	83
	l1	ı	0.90	ı	0.035

Dimension in mm / inches

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